

R-C Thermal Model Parameters

DESCRIPTION

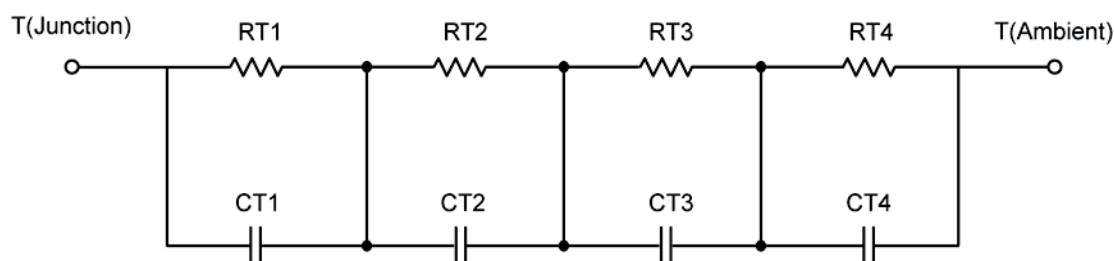
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

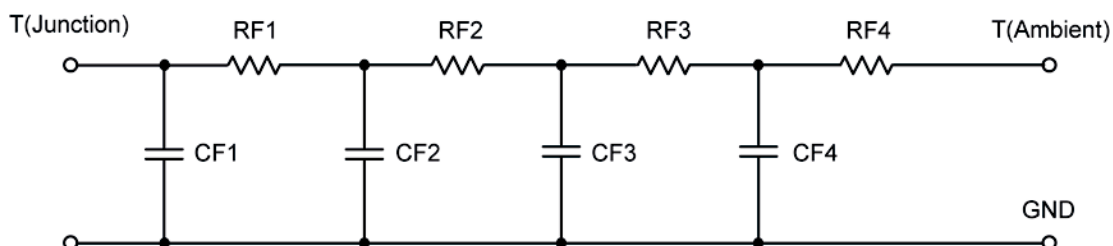
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	9.4639	N/A	2.4666
RT2	11.2169	N/A	4.8990
RT3	39.0849	N/A	9.2437
RT4	50.2369	N/A	22.3274
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.6202 m	N/A	267.7846 u
CT2	137.3540 m	N/A	4.7820 m
CT3	8.6590 m	N/A	41.1641 m
CT4	1.2638	N/A	3.9749 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	17.9100	N/A	2.4885
RF2	41.3594	N/A	16.9203
RF3	46.8135	N/A	12.1782
RF4	3.7860	N/A	7.3342
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	1.7409 m	N/A	282.7197 u
CF2	9.4163 m	N/A	1.6885 m
CF3	1.1746	N/A	2.2293 m
CF4	706.0998 m	N/A	29.0965 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

